# **Amplifier Transistors**

### **NPN Silicon**

#### **Features**

• Pb-Free Packages are Available\*

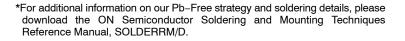
## **MAXIMUM RATINGS** ( $T_A = 25^{\circ}C$ unless otherwise noted)

Characteristic	Symbol	Value	Unit
Collector - Emitter Voltage	V <sub>CEO</sub>	40	Vdc
Collector - Base Voltage	V <sub>CBO</sub>	75	Vdc
Emitter - Base Voltage	V <sub>EBO</sub>	6.0	Vdc
Collector Current - Continuous	Ic	600	mAdc
Total Device Dissipation @ T <sub>A</sub> = 25°C Derate above 25°C	P <sub>D</sub>	625 5.0	mW mW/°C
Total Device Dissipation @ T <sub>C</sub> = 25°C Derate above 25°C	P <sub>D</sub>	1.5 12	W mW/°C
Operating and Storage Junction Temperature Range	T <sub>J</sub> , T <sub>stg</sub>	-55 to +150	°C

#### THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	200	°C/W
Thermal Resistance, Junction to Case	$R_{ heta JC}$	83.3	°C/W

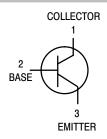
Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.





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### MARKING DIAGRAM



P2N2 = Device Code 222A = Specific Device A = Assembly Location

Y = Year WW = Work Week • Pb-Free Package

(Note: Microdot may be in either location)

#### **ORDERING INFORMATION**

Device	Package	Shipping <sup>†</sup>
P2N2222A	TO-92	5000 Units / Bulk
P2N2222AG	TO-92 (Pb-Free)	5000 Units / Bulk
P2N2222ARL1	TO-92	2000 / Tape & Ammo
P2N2222ARL1G	TO-92 (Pb-Free)	2000 / Tape & Ammo
P2N2222AZL1	TO-92	2000 / Tape & Reel
P2N2222AZL1G	TO-92 (Pb-Free)	2000 Units / Tube

<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

# **ELECTRICAL CHARACTERISTICS** ( $T_A = 25^{\circ}C$ unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Collector – Emitter Breakdown Voltage (I <sub>C</sub> = 10 mAdc, I <sub>B</sub> = 0)	V <sub>(BR)</sub> CEO	40	-	Vdc
Collector – Base Breakdown Voltage ( $I_C = 10 \mu Adc$ , $I_E = 0$ )	V <sub>(BR)</sub> CBO	75	-	Vdc
Emitter – Base Breakdown Voltage (I <sub>E</sub> = 10 μAdc, I <sub>C</sub> = 0)	V <sub>(BR)EBO</sub>	6.0	-	Vdc
Collector Cutoff Current (V <sub>CE</sub> = 60 Vdc, V <sub>EB(off)</sub> = 3.0 Vdc)	I <sub>CEX</sub>	_	10	nAdc
Collector Cutoff Current $(V_{CB} = 60 \text{ Vdc}, I_E = 0)$ $(V_{CB} = 60 \text{ Vdc}, I_E = 0, T_A = 150^{\circ}\text{C})$	Ісво	_ _ _	0.01 10	μAdc
Emitter Cutoff Current $(V_{EB} = 3.0 \text{ Vdc}, I_C = 0)$	I <sub>EBO</sub>	-	10	nAdc
Collector Cutoff Current (V <sub>CE</sub> = 10 V)	I <sub>CEO</sub>	-	10	nAdc
Base Cutoff Current (V <sub>CE</sub> = 60 Vdc, V <sub>EB(off)</sub> = 3.0 Vdc)	I <sub>BEX</sub>	-	20	nAdc
ON CHARACTERISTICS				
DC Current Gain $ \begin{array}{l} (I_C=0.1 \text{ mAdc, } V_{CE}=10 \text{ Vdc}) \\ (I_C=1.0 \text{ mAdc, } V_{CE}=10 \text{ Vdc}) \\ (I_C=10 \text{ mAdc, } V_{CE}=10 \text{ Vdc}) \\ (I_C=10 \text{ mAdc, } V_{CE}=10 \text{ Vdc}, T_A=-55^{\circ}C) \\ (I_C=150 \text{ mAdc, } V_{CE}=10 \text{ Vdc, } (Note 1) \\ (I_C=150 \text{ mAdc, } V_{CE}=1.0 \text{ Vdc)} \text{ (Note 1)} \\ (I_C=500 \text{ mAdc, } V_{CE}=10 \text{ Vdc)} \text{ (Note 1)} \end{array} $	h <sub>FE</sub>	35 50 75 35 100 50 40	- - - 300 -	_
Collector – Emitter Saturation Voltage (Note 1) $(I_C = 150 \text{ mAdc}, I_B = 15 \text{ mAdc})$ $(I_C = 500 \text{ mAdc}, I_B = 50 \text{ mAdc})$	V <sub>CE(sat)</sub>	- -	0.3	Vdc
Base – Emitter Saturation Voltage (Note 1) (I <sub>C</sub> = 150 mAdc, I <sub>B</sub> = 15 mAdc) (I <sub>C</sub> = 500 mAdc, I <sub>B</sub> = 50 mAdc)	V <sub>BE(sat)</sub>	0.6	1.2	Vdc
SMALL-SIGNAL CHARACTERISTICS	l l			1
Current – Gain – Bandwidth Product (Note 2) (I <sub>C</sub> = 20 mAdc, V <sub>CE</sub> = 20 Vdc, f = 100 MHz)C	f <sub>T</sub>	300	-	MHz
Output Capacitance (V <sub>CB</sub> = 10 Vdc, I <sub>E</sub> = 0, f = 1.0 MHz)	C <sub>obo</sub>	_	8.0	pF
Input Capacitance (V <sub>EB</sub> = 0.5 Vdc, I <sub>C</sub> = 0, f = 1.0 MHz)	C <sub>ibo</sub>	-	25	pF
Input Impedance ( $I_C$ = 1.0 mAdc, $V_{CE}$ = 10 Vdc, f = 1.0 kHz) ( $I_C$ = 10 mAdc, $V_{CE}$ = 10 Vdc, f = 1.0 kHz)	h <sub>ie</sub>	2.0 0.25	8.0 1.25	kΩ
Voltage Feedback Ratio ( $I_C = 1.0 \text{ mAdc}$ , $V_{CE} = 10 \text{ Vdc}$ , $f = 1.0 \text{ kHz}$ ) ( $I_C = 10 \text{ mAdc}$ , $V_{CE} = 10 \text{ Vdc}$ , $f = 1.0 \text{ kHz}$ )	h <sub>re</sub>	-	8.0 4.0	X 10 <sup>-4</sup>
Small–Signal Current Gain ( $I_C = 1.0 \text{ mAdc}$ , $V_{CE} = 10 \text{ Vdc}$ , $f = 1.0 \text{ kHz}$ ) ( $I_C = 10 \text{ mAdc}$ , $V_{CE} = 10 \text{ Vdc}$ , $f = 1.0 \text{ kHz}$ )	h <sub>fe</sub>	50 75	300 375	-
Output Admittance ( $I_C = 1.0 \text{ mAdc}$ , $V_{CE} = 10 \text{ Vdc}$ , $f = 1.0 \text{ kHz}$ ) ( $I_C = 10 \text{ mAdc}$ , $V_{CE} = 10 \text{ Vdc}$ , $f = 1.0 \text{ kHz}$ )	h <sub>oe</sub>	5.0 25	35 200	μMhos
Collector Base Time Constant (I <sub>E</sub> = 20 mAdc, V <sub>CB</sub> = 20 Vdc, f = 31.8 MHz)	rb′C <sub>c</sub>	-	150	ps
Noise Figure (I <sub>C</sub> = 100 $\mu$ Adc, V <sub>CE</sub> = 10 Vdc, R <sub>S</sub> = 1.0 $\mu$ Adc, f = 1.0 kHz)	N <sub>F</sub>	-	4.0	dB

<sup>1.</sup> Pulse Test: Pulse Width  $\leq$  300  $\mu$ s, Duty Cycle  $\leq$  2.0%. 2. f<sub>T</sub> is defined as the frequency at which  $|h_{fe}|$  extrapolates to unity.

**ELECTRICAL CHARACTERISTICS** (T<sub>A</sub> = 25°C unless otherwise noted) (Continued)

	Symbol	Min	Max	Unit	
SWITCHING CHARACTERISTICS					
Delay Time	$(V_{CC} = 30 \text{ Vdc}, V_{BE(off)} = -2.0 \text{ Vdc},$	t <sub>d</sub>	-	10	ns
Rise Time	I <sub>C</sub> = 150 mAdc, I <sub>B1</sub> = 15 mAdc) (Figure 1)	t <sub>r</sub>	-	25	ns
Storage Time	(V <sub>CC</sub> = 30 Vdc, I <sub>C</sub> = 150 mAdc,	t <sub>s</sub>	-	225	ns
Fall Time	$I_{B1} = I_{B2} = 15 \text{ mAdc}$ (Figure 2)	t <sub>f</sub>	-	60	ns

### **SWITCHING TIME EQUIVALENT TEST CIRCUITS**

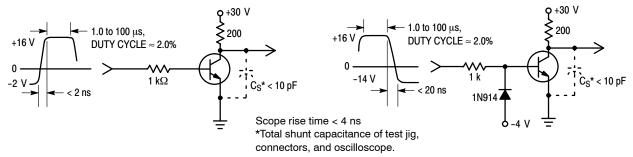


Figure 1. Turn-On Time Figure 2. Turn-Off Time

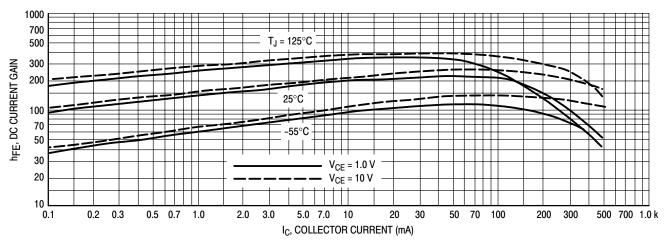


Figure 4. DC Current Gain

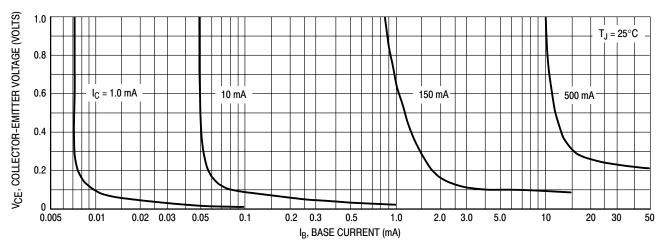


Figure 3. Collector Saturation Region

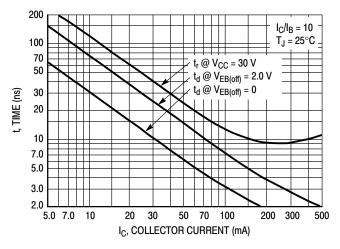


Figure 5. Turn - On Time

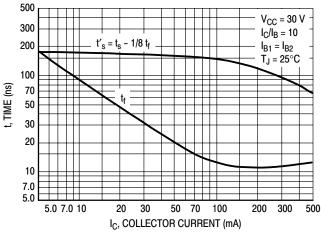


Figure 6. Turn - Off Time

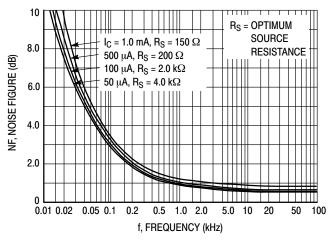


Figure 7. Frequency Effects

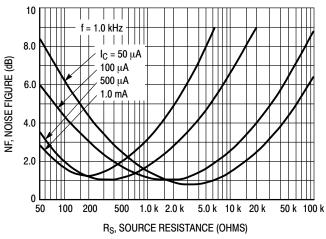


Figure 8. Source Resistance Effects

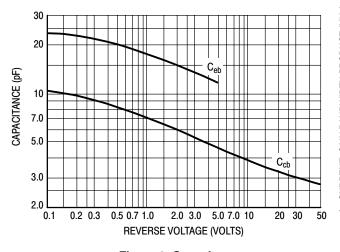


Figure 9. Capacitances

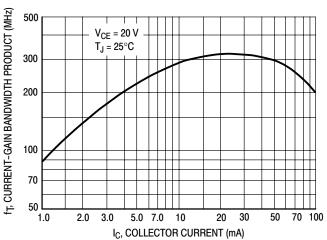
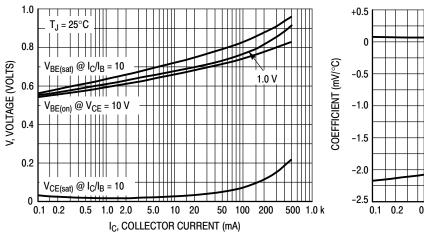
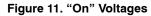


Figure 10. Current-Gain Bandwidth Product





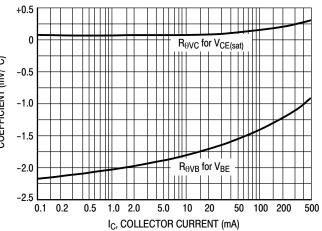
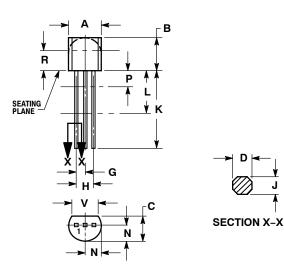


Figure 12. Temperature Coefficients

#### PACKAGE DIMENSIONS

TO-92 (TO-226) CASE 29-11 **ISSUE AL** 



#### NOTES:

- DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
- CONTROLLING DIMENSION: INCH.
  CONTOUR OF PACKAGE BEYOND DIMENSION R IS UNCONTROLLED.
  LEAD DIMENSION IS UNCONTROLLED IN P AND
- BEYOND DIMENSION K MINIMUM

	INC	HES	MILLIMETERS		
DIM	MIN	MAX	MIN	MAX	
Α	0.175	0.205	4.45	5.20	
В	0.170	0.210	4.32	5.33	
С	0.125	0.165	3.18	4.19	
D	0.016	0.021	0.407	0.533	
G	0.045	0.055	1.15	1.39	
Н	0.095	0.105	2.42	2.66	
J	0.015	0.020	0.39	0.50	
K	0.500		12.70		
L	0.250		6.35		
N	0.080	0.105	2.04	2.66	
P		0.100		2.54	
R	0.115		2.93		
٧	0.135		3.43		

STYLE 17:

PIN 1. COLLECTOR 2. BASE

- **EMITTER**

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